

BYC75W-1200P

Hyperfast power diode

Rev.03 - 25 January 2021

Product data sheet

1. General description

EEPP[™] - Efficiency Enhanced Pt Planar rectifier in a TO247-2L plastic package.

2. Features and benefits

- Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- Planar termination structure
- High operating temperature capability (T_{j(max)} = 175°C)
- Higher I_{FSM} capability

3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter Conditions			Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage	se 1200			V		
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 75$ °C; Fig. 1; Fig. 2; Fig. 3	75			A	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 75 °C; square-wave pulse	150			A	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600			A	
		$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse		6	60		А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 75 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.8	3.3	V
		I _F = 75 A; T _j = 150 °C; <u>Fig. 6</u>		-	2.2	-	V
Dynamic	characteristics				1		
t _{rr}	reverse recovery time $I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; \frac{\text{Fig. 7}}{2}$			-	-	85	ns
Avalanch	ne energy						
E _{AS}	non-repetitive avalanche energy	I _R = 1.6 A; T _{j(init)} = 25 °C; L = 40 mH		50	-	-	mJ

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod	6 K A TO247-2L	

6. Ordering information

Table 3. Ordering information						
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC75W-1200P	TO247-2L	BYC75W-1200PQ	Tube	30	TO247A-2L	22-Jun-2017

7. Marking

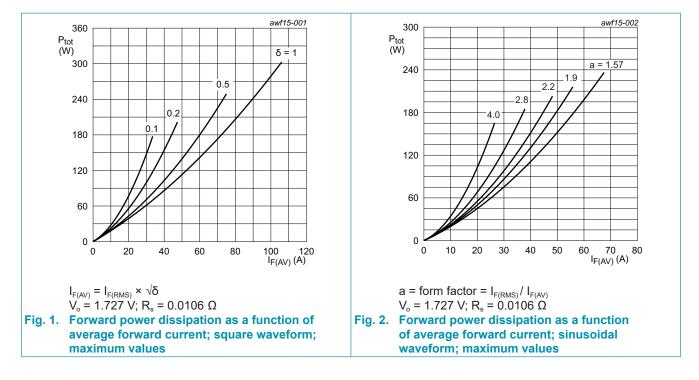
Table 4. Marking codes				
Type number	Marking codes			
BYC75W-1200P	BYC75W 1200P			

8. Limiting values

Table 5. Limiting values

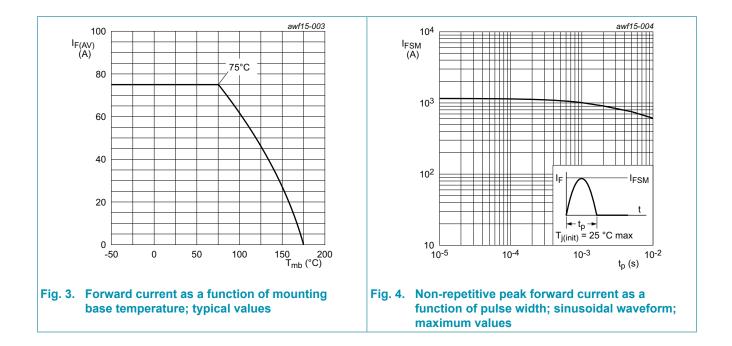
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V _R	reverse voltage	DC	1200	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 75 °C; Fig. 1; Fig. 2; Fig. 3	75	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 75 °C; square-wave pulse	150	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	660	А
T _{stg}	storage temperature		-55 to 175	°C
Tj	junction temperature		-55 to 175	°C



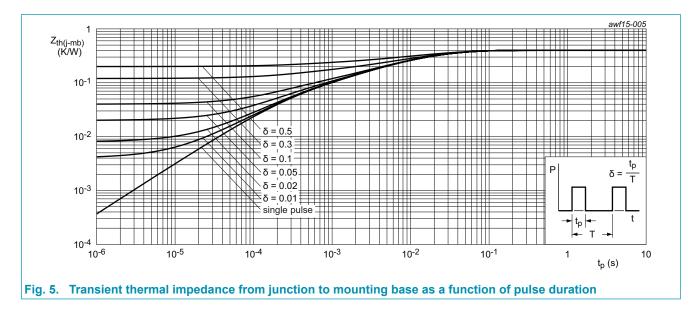
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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.4	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

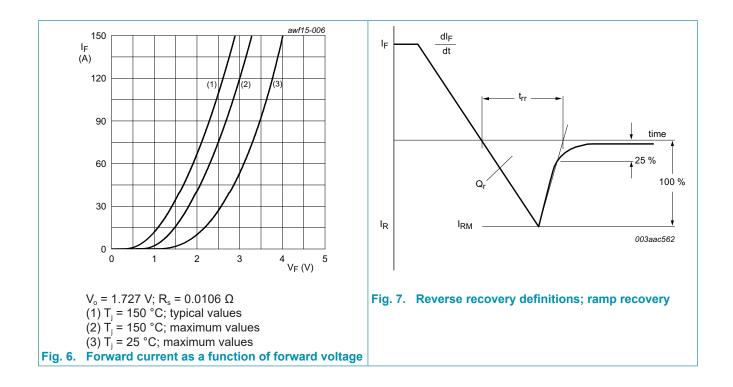


10. Characteristics

Symbol	Parameter	Conditions	M	in Typ	Max	Unit
Static ch	aracteristics	1				_
V _F	forward current	I _F = 75 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.8	3.3	V
		I _F = 75 A; T _j = 150 °C; <u>Fig. 6</u>	-	2.2	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	250	μA
		V _R = 600 V; T _j = 125 °C	-	-	2	mA
Dynamic	characteristics	l				
Q _r reverse charge	reverse charge	$I_{F} = 50 \text{ A}; V_{R} = 400 \text{ V}; \text{ d}I_{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; T_{j} = 25 \text{ °C}; Fig. 7$	-	1282	-	nC
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	3729	-	nC
		$I_{F} = 50 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A}/\mu\text{s}; \\ T_{j} = 150 ^{\circ}\text{C}; \underline{Fig. 7}$	-	4608	-	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	-	85	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	113	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 ^\circ\text{C}; \text{ Fig. 7}$	-	232	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 150 ^\circ\text{C}; \text{ Fig. 7}$	-	265	-	A
I _{RM}	peak reverse recovery current	I _F = 50 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	22.4	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 ^\circ\text{C}; \text{ Fig. 7}$	-	32	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 150 ^\circ\text{C}; \text{ Fig. 7}$	-	34.6	-	A
Avalanch	ne energy					
E _{AS}	non-repetitive avalanche energy	$I_R = 1.6 \text{ A}; T_{j(init)} = 25 \text{ °C}; L = 40 \text{ mH}$	50) -	-	mJ

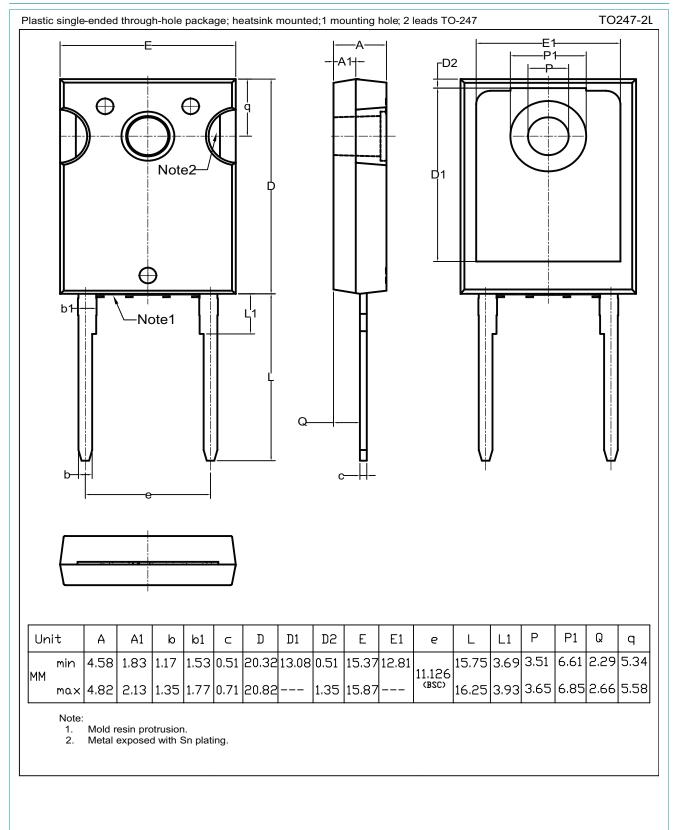
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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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